

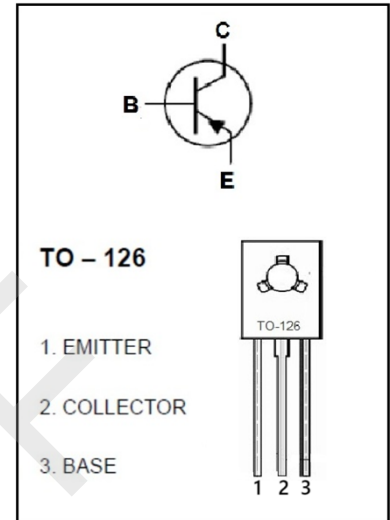
PNP Silicon Transistor

2SA1220/2SA1220A

- Complementary to 2SC2690/2SC2690A
- Package: TO-126

Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Rating		Unit
Collector-base voltage	BV_{CBO}	2SA1220	-120	V
		2SA1220A	-160	
Collector-emitter voltage	BV_{CEO}	2SA1220	-120	V
		2SA1220A	-160	
Emitter-base voltage	BV_{EBO}	-5		V
Collector current	I_C	-1.2		A
Peak Collector current	I_{CM}	-2.5		A
Collector Power Dissipation	P_C	1.2		W
	P_C	Ta = 25°C	20	
Junction Temperature	T_j	150		°C
Storage Temperature	T_{stg}	-55 ~ +150		°C



Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
collector-base cut-off current	I_{CBO}	$V_{CB} = -120V, I_E = 0$			-1	μA
emitter-base cut-off current	I_{EBO}	$V_{EB} = -3V, I_C = 0$			-1	μA
DC current gain	H_{FE1}	$V_{CE} = -5V, I_C = -0.3A$	60		320	
	H_{FE2}	$V_{CE} = -5V, I_C = -5mA$	35			
collector-emitter saturation voltage	V_{CESAT}	$I_C = -1A, I_B = -0.2A$			-0.7	V
Base-Emitter Voltage	V_{BESAT}	$I_C = -1A, I_B = -0.2A$			-1.3	
Transition frequency	f_T	$V_{CE} = -5V, I_C = -0.2A$		175		MHz

Classification of H_{FE1}

Rank	R	Q	P
Range	60-120	100-200	160-320